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NAKAYAMA ET AL.

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	Saddow et al, "Therm	ial Capacitance Spe	ectroscopy of Epitaxial 3C a	ind 6H-Sic pn J	unction Dio	des Gro	wn Sic
	By Side on a 6H-SiC	Substrate", Applied	Physics Letters, AIP, Amer	rican Institute o	f Physics, M	lelville, l	NY, vo
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